

Investigation of an emission current regulation circuit in the frequency domain

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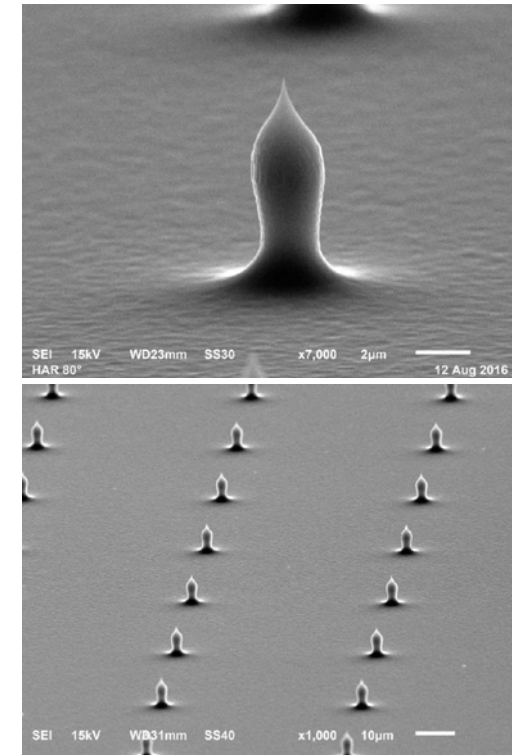
Content

- Motivation
- Investigated micro-structures
- Measurement setup and characterization
- Intentional noise modulation onto the emission current
- Noise behaviour of the samples using the current regulation circuit
- Conclusion

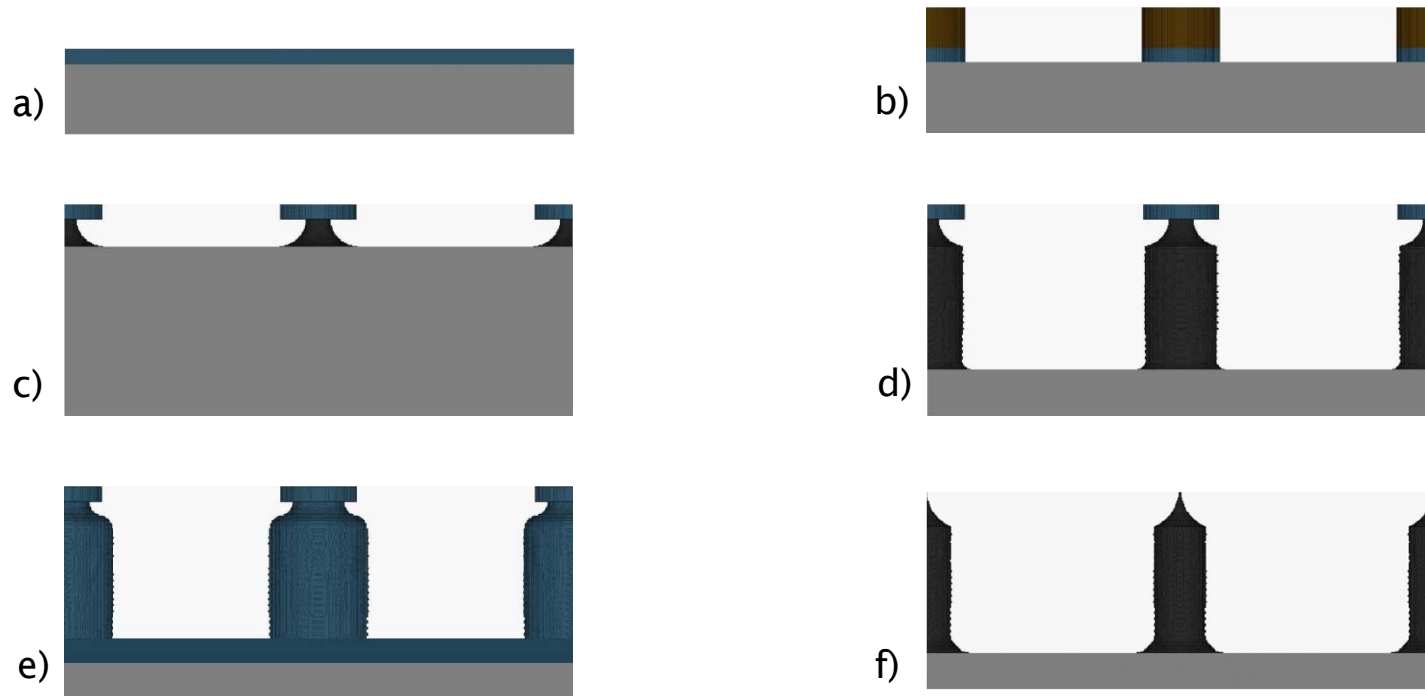
- Effective electron sources compared to other electron sources (tubes → heat losses)
- No thermal processes → Fast switching
- Used by different devices
 - X-Ray sources
 - Vacuum gauges
 - Electron guns
 - ...
- Problem: Stability and electron yield depends on doping
 - Metal-like emitters results in higher current values but lower stability
 - P-type emitters have high stability but lower current values
- Use of a current regulation circuit
 - Setting a desired target emission current
 - Suppress noisy frequencies of the emission current
 - Use frequency domain to check the regulation circuit performance

Investigated micro-structures

sample	A	B
substrate	p-type Si	undoped Si
dopant concentration	10^{15} - 10^{16}cm^{-3}	10^{12} - 10^{13}cm^{-3}
specific resistivity	1-10 Ωcm	1-10k Ωcm
coating	none	Au 10nm
total height H	8 μm	8 μm
pillar diameter \varnothing_p	2 μm	2 μm
apex radii R	<20nm	<30nm
array size	10 x 10	10 x 10
pitch	50 μm	50 μm
work function	4.9eV	5.1eV (Au)



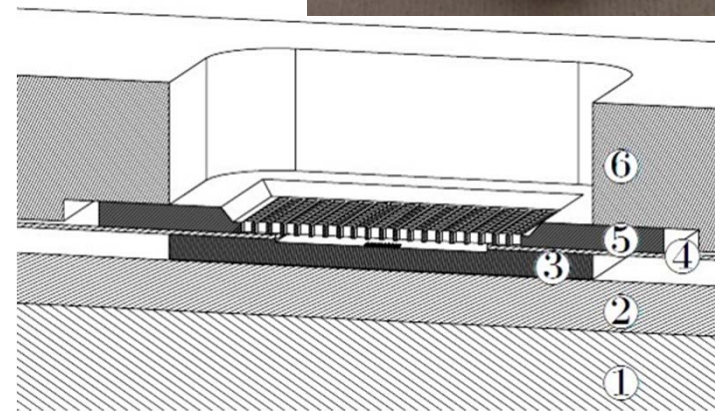
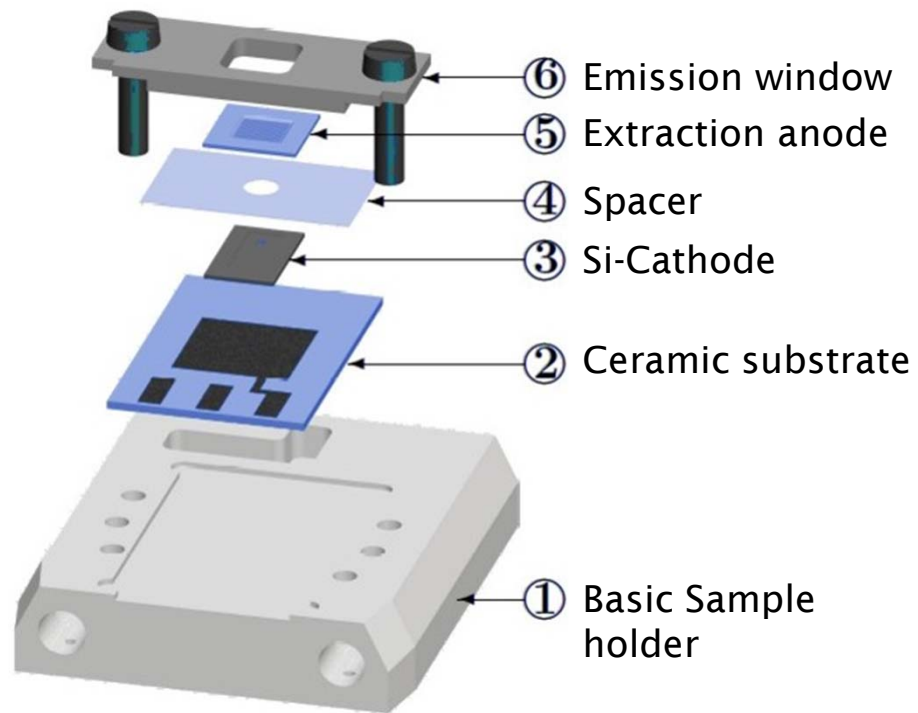
Investigated micro-structures - Fabrication process^[1]



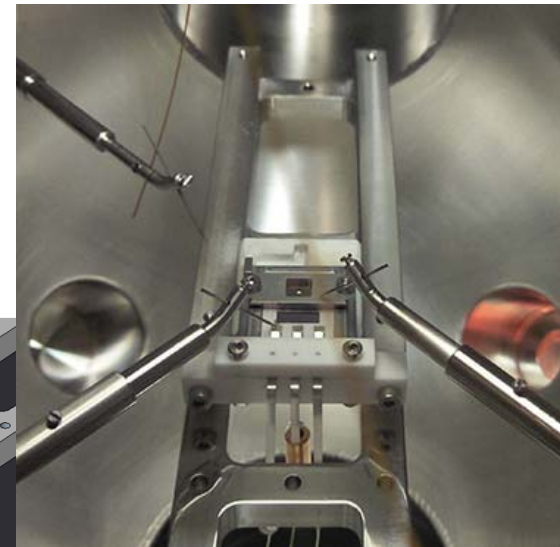
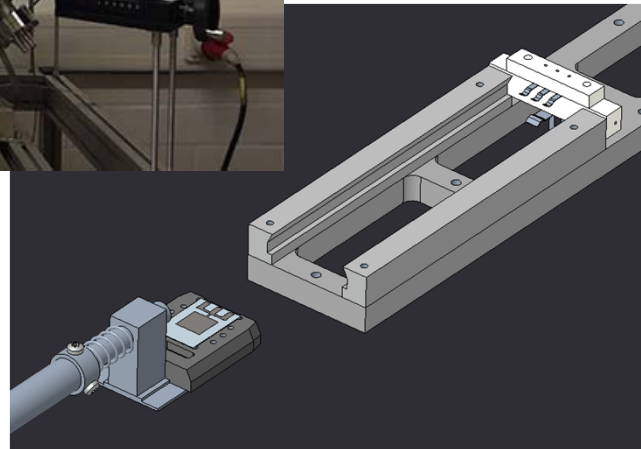
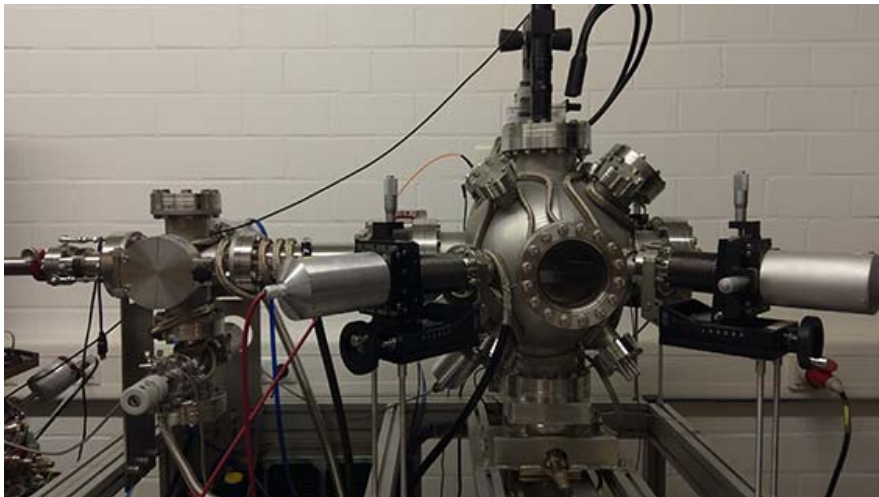
[1] R. Lawrowski, C. Langer, C. Prommesberger, F. Dams, M. Bachmann, and R. Schreiner, "Fabrication and simulation of silicon structures with high aspect ratio for field emission devices," 2014, pp. 193-194.

Measurement setup

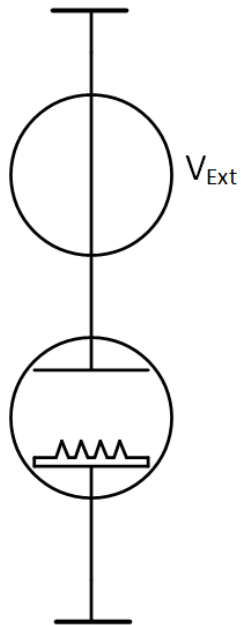
Sample holder



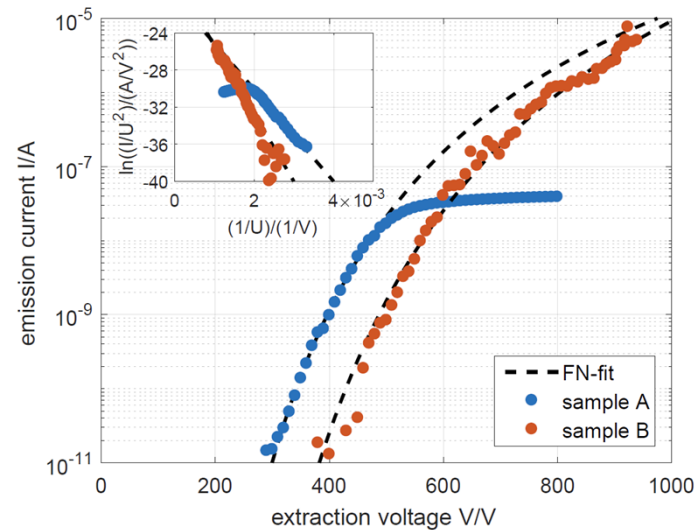
Vacuum chamber and installation



Characterization

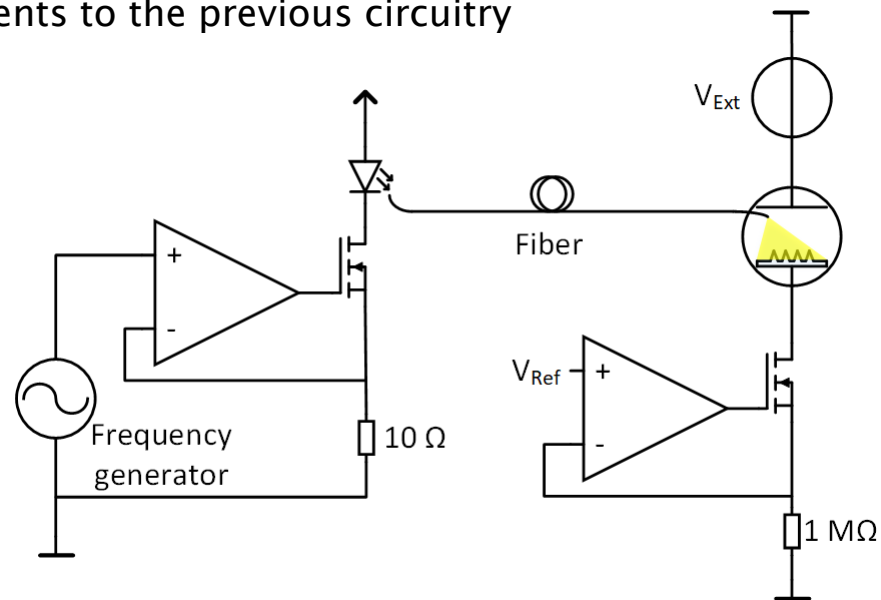


sample	A	B
onset Voltage (1 nA)	≈400V	≈490V
max. emission current	39nA	4.1μA
field enhancement factor β	≈750	≈540
emission behaviour	saturation	metal-like



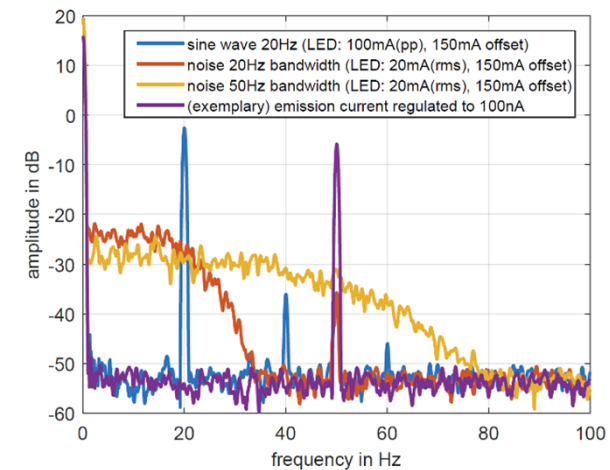
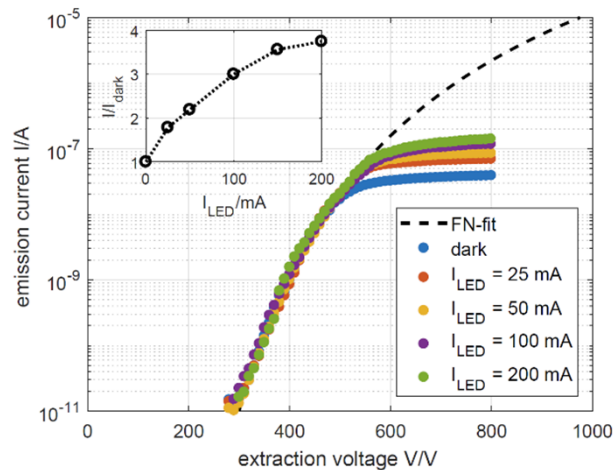
Emulate an unstable emission behaviour – Extended circuit

- Exploiting the lightning effect of p-type silicon emitters
- Additional elements to the previous circuitry

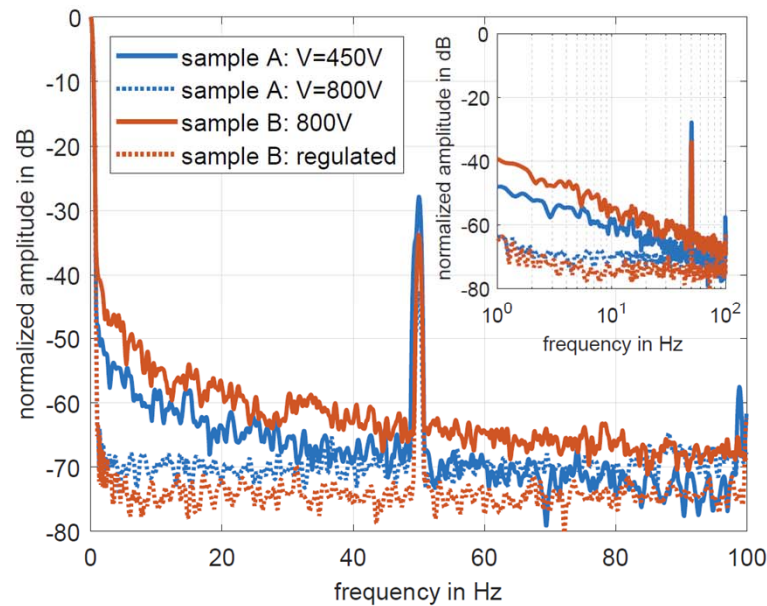


Emulate an unstable emission behaviour on p-type emitters (sample A)

- Current shift up to higher currents due to brighter illumination
- Modulation of sample-signals and -noise to the emission current
- Suppression of the noise by using the regulation circuit



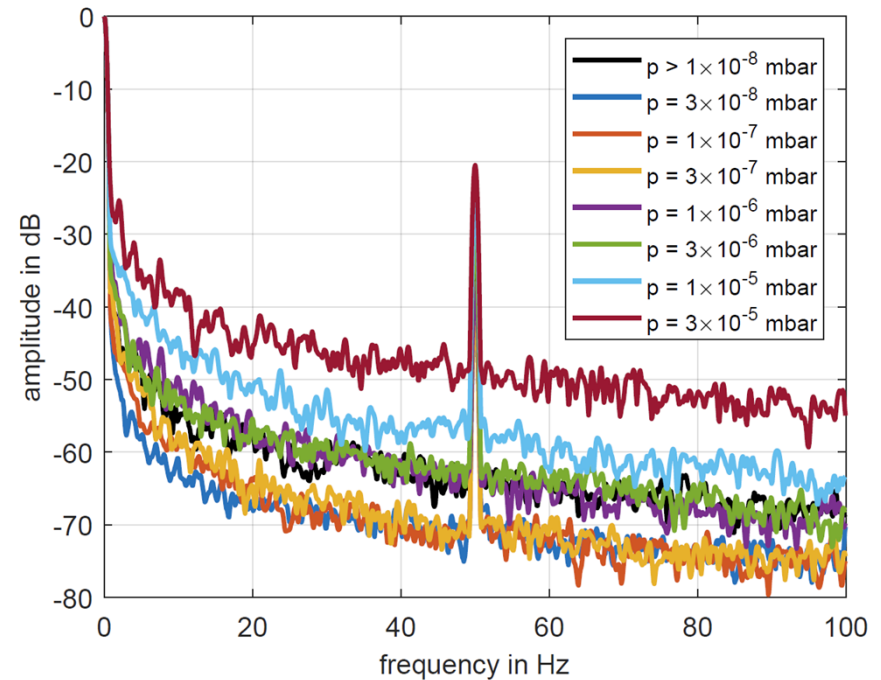
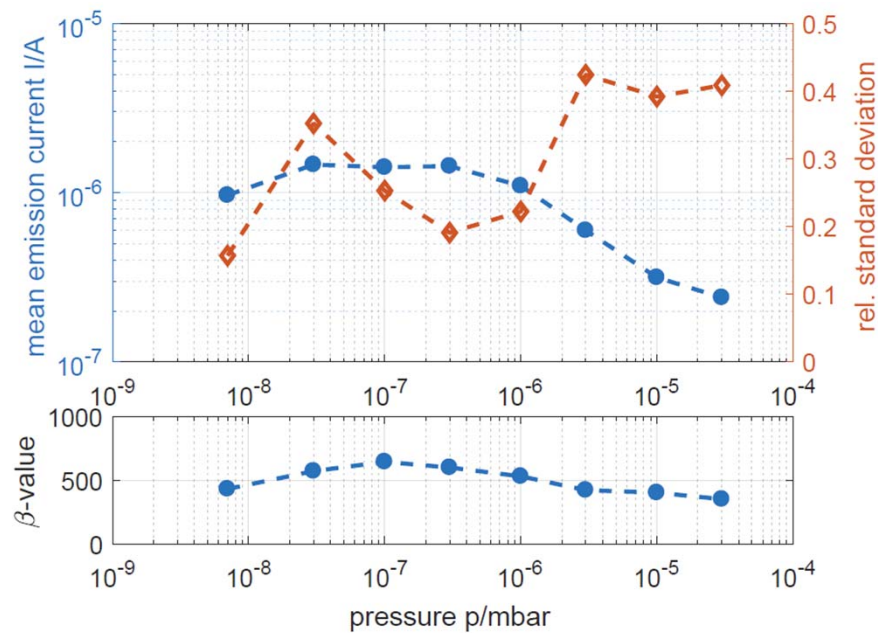
Stability of the emission current under real conditions



sample A	below saturation	in saturation
extraction voltage	450 V	800 V
emission current	5.6 nA	39 nA
rel. standard deviation	$\pm 16 \%$	$\pm 0.3 \%$

sample B	no regulation	regulated
extraction voltage	800 V	N/A
emission current	0.96 μ A	1 μ A
rel. standard deviation	$\pm 16 \%$	$\pm 0.4 \%$

Pressure influence – short term measurements



1. Our conventional field emission setup is extended due to noise emulation exploiting p-type lightning effects by a:
 - current regulation circuit
 - supply circuit for noise emulation LED
 2. Sample A emission follows the LED-Noise like expected
 3. The regulation circuit has an excellent regulation behaviour
 - Suppression of the field emission noise
 - High stability of emission current
 - Variation of extraction voltage (problematic for applications)
 4. Typically pressure dependence is observed like expected
 5. Powerline has a non-neglectable impact in our emission current
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- More compact regulation circuit design and improved shielding for the entire measurement setup
 - Measurement of pressure dependence using regulation circuit
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